

Date Faxed: December 20, 2005

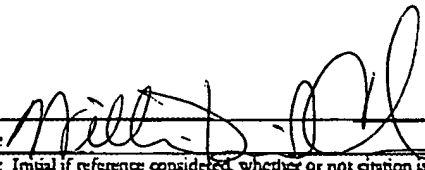
Sheet 1 of 1

Form 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Docket Number: G&C 30794.93-US-WO	Application Number: 10/537,644
	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 6, 2005	Group Art Unit: Not yet assigned - 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	

FOREIGN PATENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
		Amano, H. et al., "Stress and Defect Control in GaN Using Low Temperature Interlayers," Jpn. J. Appl. Phys. Vol. 37 (1998), pp. L 1540-L 1542

EXAMINER: 	DATE CONSIDERED: <u>MARCH 30, 2006</u>
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

*Substitute Disclosure Statement Form (PTO-1449)

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